PDFN3×3A-8L N MOS

N-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

V_{DS} (V) = 40V

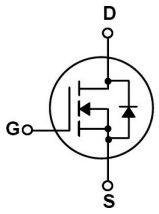
I_D =45 A (V_{GS} = ±20V)

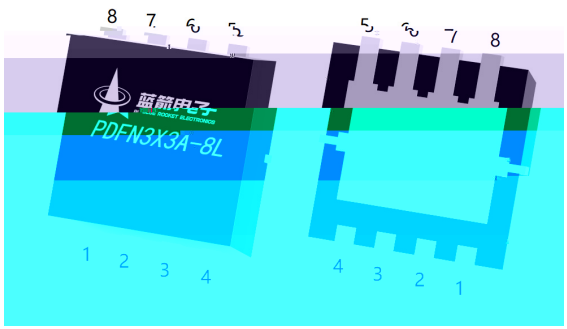
$R_{DS(ON)}$@10V ≤ 8mR(Typ.6.4mR)

AEC-Q101 Qualified to AEC-Q101 Standards for High Reliability, HF Product.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies, Meet the stringent requirements of automotive applications.





See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	40	V
Drain Current	I_D(Tc=25)	45	A
Drain Current - Pulsed	I_{DM}	109((54)583(A	)]TJET55

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

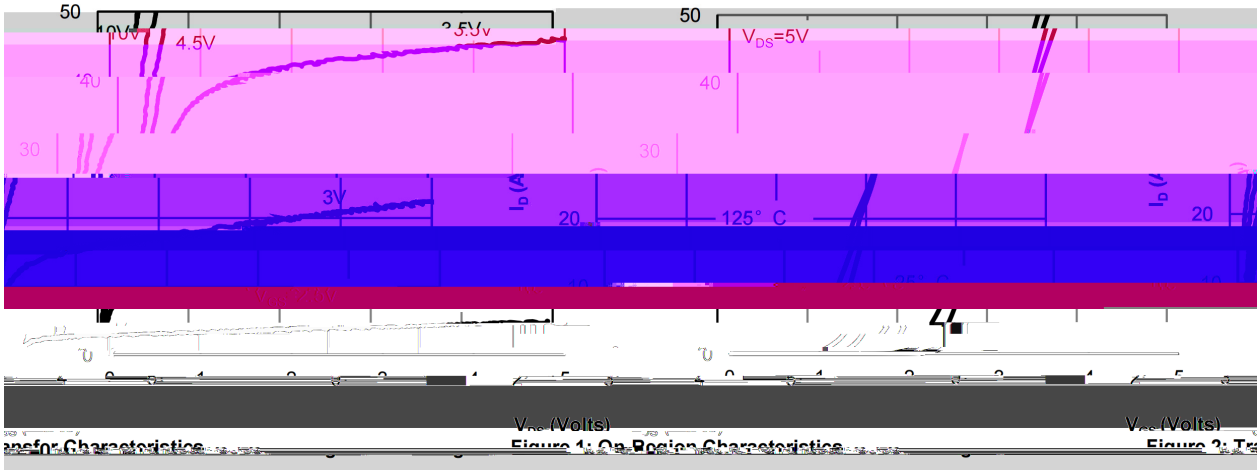
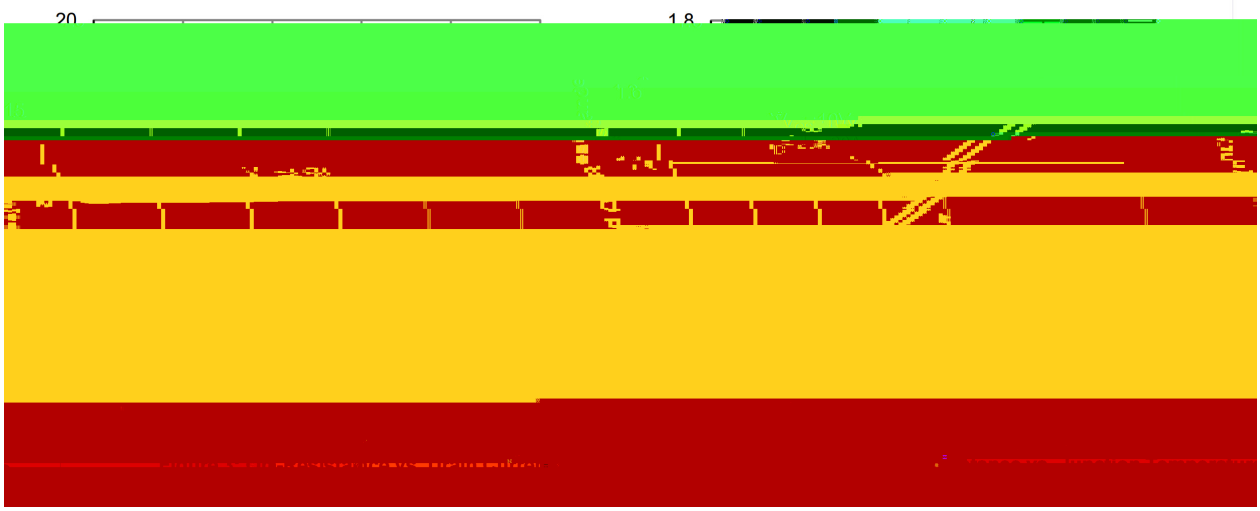


Figure 1: On-Region Characteristics

Figure 2: Tr



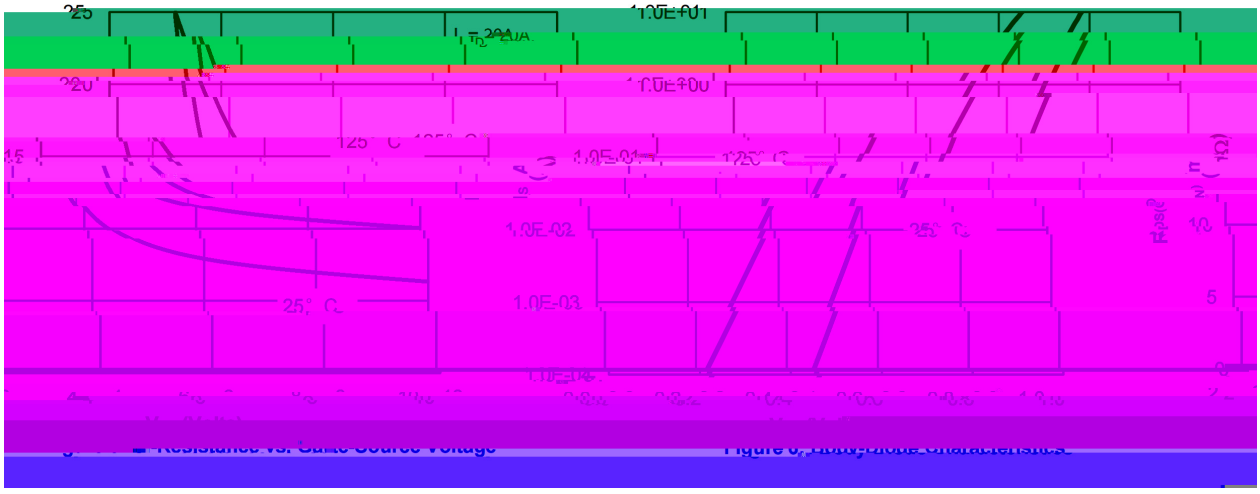
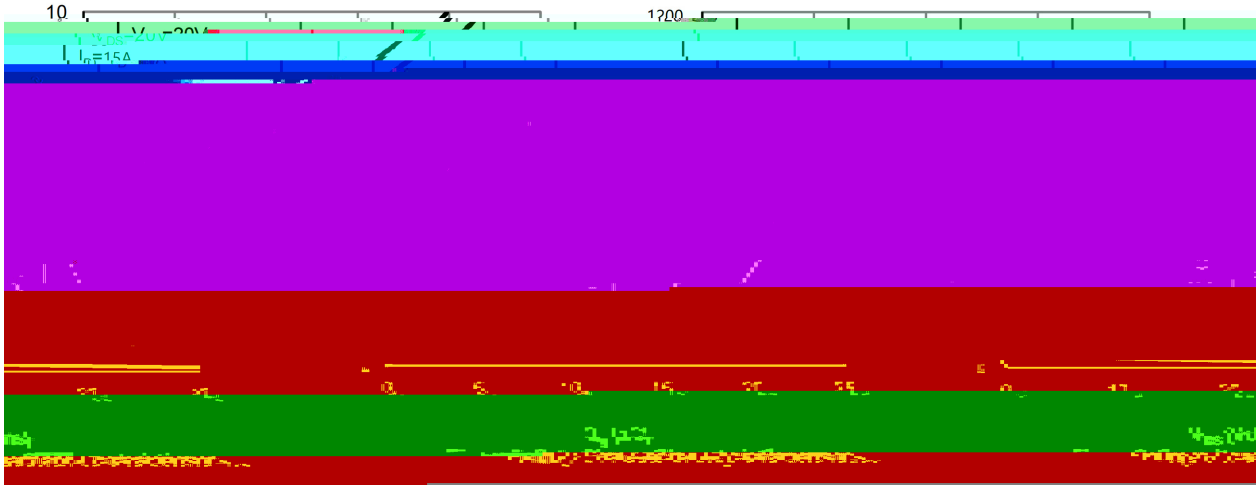
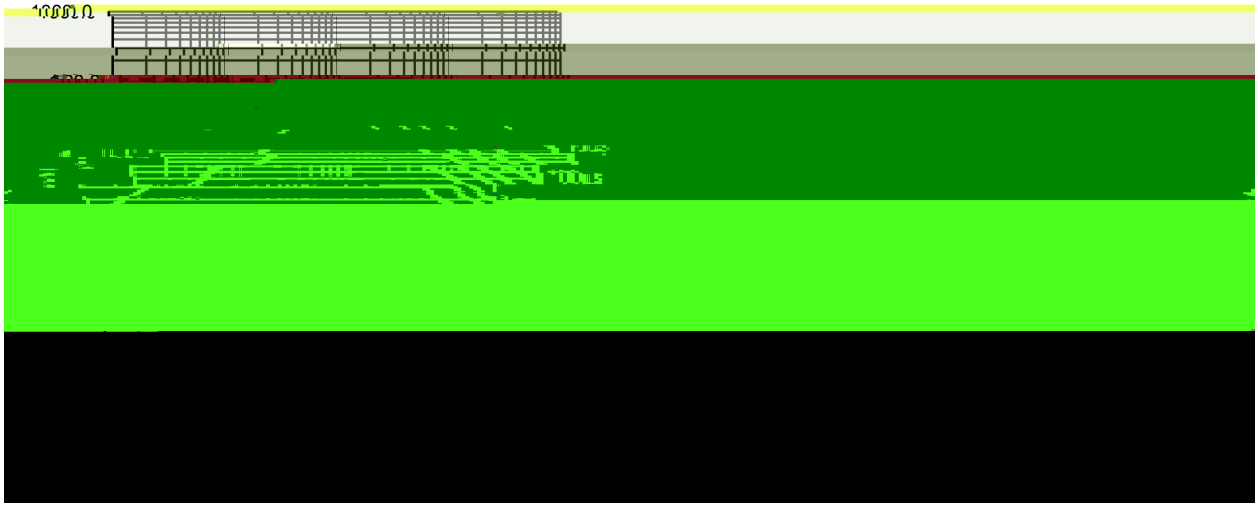


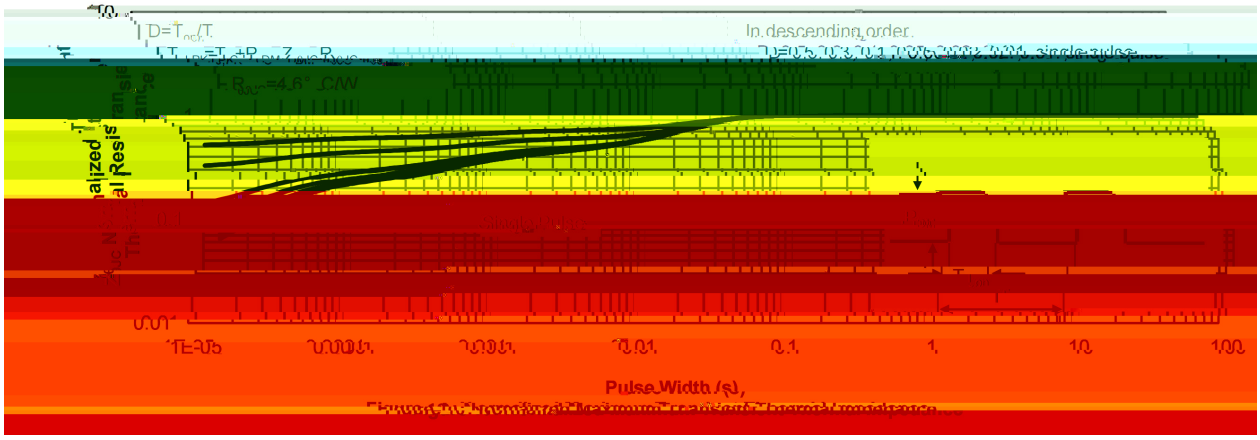
Figure 5: Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

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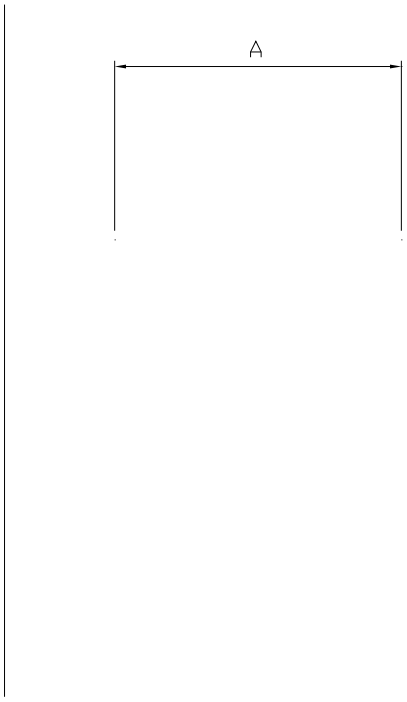




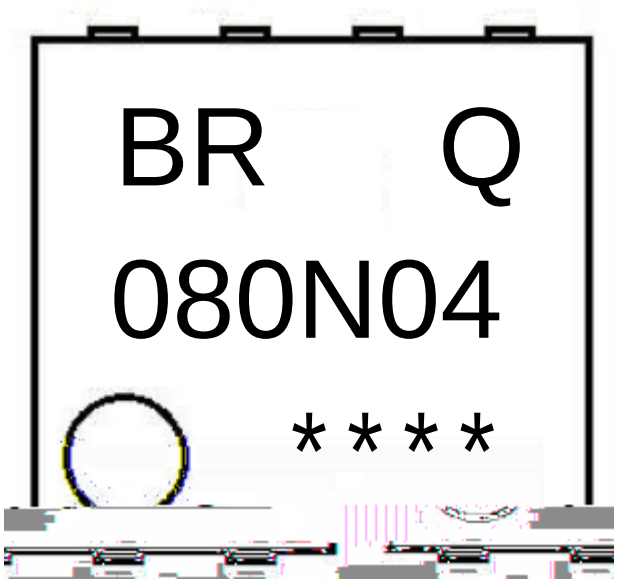

D=T
In descending order
Pulse Width /s)

PDFN3X3A-8L

Unit:mm



Rev.00



BR

Q

080N04

****

Note:

BR:	Company Code
Q:	Au5imobile halogen-free product Code
080N04:	Product Type Code
****:	Lot No. Code, code change with Lot No